DESCRIPTION

The 2SA1203-O & 2SA1203-Y is available in SOT-89 package.

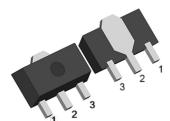
FEATURE

- · Suitable for Output Stage of 3 Watts Amplifier
- · Small Flat Package
- P_C = 1 to 2W (mounted on ceramic substrate)
- · Complementary to 2SC2883

ORDERING INFORMATION

| Package Type | Part Number | |
|--|-------------------|--|
| 00 TO2 | 2SA1203-O | |
| SOT-89 | 2SA1203-Y | |
| SPQ | SPQ 1,000pcs/Reel | |
| AiT provides all RoHS Compliant Products | | |

PIN DESCRIPTION



SOT-89

h_{FE} CLASSIFICATION

| Rank | Range |
|------|-----------|
| 0 | 100 ~ 200 |
| Υ | 160 ~ 320 |

| PIN# | DESCRIPTION | | |
|------|-------------|--|--|
| 1 | Base | | |
| 2 | Collector | | |
| 3 | Emitter | | |

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified.

| , | |
|--|---------------|
| V _{CBO} , Collector-Base Voltage | -30 V |
| V _{CEO} , Collector-Emitter Voltage | -30 V |
| V _{EBO} , Emitter-Base Voltage | -5 V |
| Ic, Collector Current | -1.5 A |
| I _B , Base Current | -0.3 A |
| P _C , Collector Power Dissipation | 500 mW |
| Pc (1), Collector Power Dissipation | 1000 mW |
| T _J , Junction Temperature | 150 °C |
| T _{stg} , Storage Temperature Range | -55 ~ +150 °C |

⁽¹⁾ Mounted on ceramic substrate (250 mm² x 0.8 t)

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 T_A =25°C unless otherwise specified.

| Parameter | Symbols | Conditions | Min. | Тур. | Max. | Unit |
|--------------------------------------|-----------------------|---|------|------|------|------|
| Collector Cut-off Current | Ісво | V _{CB} = -30 V, I _E = 0 | ı | - | -0.1 | μΑ |
| Emitter Cut-off Current | I _{EBO} | V _{EB} = -5 V, I _C = 0 | - | - | -0.1 | μΑ |
| Collector-Emitter Breakdown Voltage | V _(BR) CEO | I _C = -10 mA, I _B = 0 | -30 | - | - | V |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | I _E = -1 mA, I _c = 0 | -5 | - | - | V |
| DC Current Gain | h _{FE} | V _{CE} = -2 V, I _C = -500 mA | 100 | - | 320 | - |
| Collector-Emitter Saturation Voltage | V _{CE} (sat) | $I_C = -1.5 \text{ A},$ $I_B = -0.03 \text{ A},$ | - | - | -2 | V |
| Base-Emitter Voltage | V _{ВЕ} | V _{CE} = -2 V, I _C = -500 mA | - | - | -1 | V |
| Transition Frequency | f⊤ | V _{CE} = -2 V, I _C = -500 mA | 1 | 120 | 1 | MHz |
| Collector Output Capacitance | C _{ob} | $V_{CB} = -10 \text{ V},$ $I_E = 0$ $f = 1 \text{ MHz}$ | - | - | 50 | pF |



TYPICAL CHARACTERISTICS

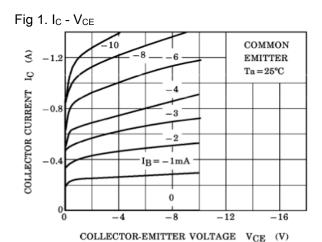


Fig 3. V_{CE(sat)} - I_C

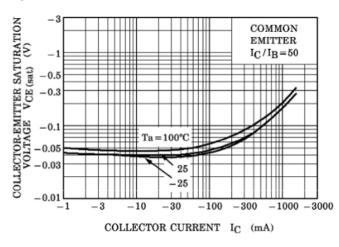


Fig 5. SAFE OPERATING AREA

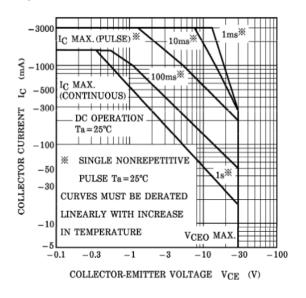


Fig 2. hFE - I_C

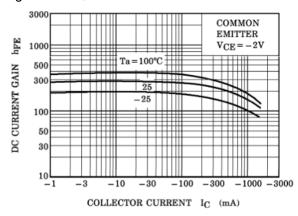


Fig 4. Ic - VBE

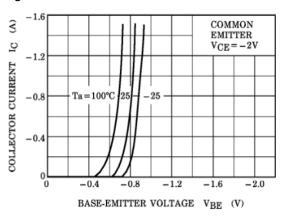
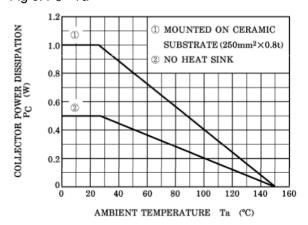


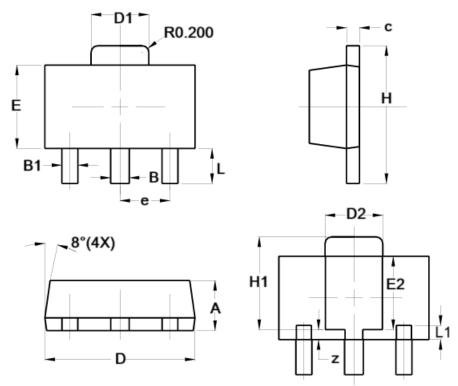
Fig 6. Pc - Ta





PACKAGE INFORMATION

Dimension in SOT-89 (Unit: mm)



| Comple of | Millin | neter | | |
|-----------|------------|-------|--|--|
| Symbol | Min. | Max. | | |
| А | 1.400 | 1.600 | | |
| В | 0.500 | 0.620 | | |
| B1 | 0.420 | 0.540 | | |
| С | 0.350 | 0.430 | | |
| D | 4.440 | 4.600 | | |
| D1 | 1.620 | 1.830 | | |
| D2 | 1.610 | 1.810 | | |
| E | 2.400 | 2.600 | | |
| E2 | 2.050 | 2.350 | | |
| е | 1.500 TYP. | | | |
| Н | 3.950 | 4.250 | | |
| H1 | 2.630 | 2.930 | | |
| L | 0.900 | 1.200 | | |
| L1 | 0.327 | 0.527 | | |
| Z | 0.200 | 0.400 | | |

2SA1203
TRANSISTOR
SILICON PNP EPITAXIAL TYPE TRANSISTOR

IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc. integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or server property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.

REV1.0 - JAN 2024 RELEASED -

- 5 -